DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max T_A = +25°C
30V	3Ω @ V_{GS} = 4.5V	350mA
	7Ω @ V_{GS} = 2.5V	

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- DC-DC Converters
- Backlighting

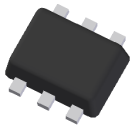
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

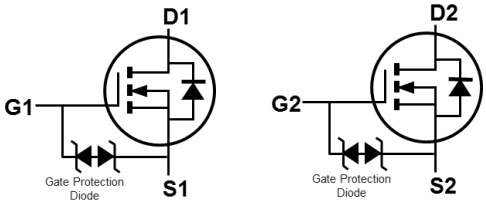
Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

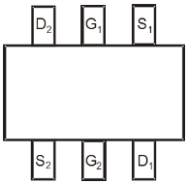
SOT563



Top View



Internal Schematic



Top View
Pin Out

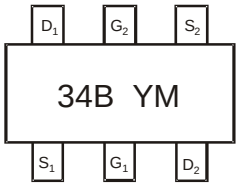
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DMN33D9LV-7	34B	7	8	3,000
DMN33D9LV-7A	34B	7	8	3,000
DMN33D9LV-13	34B	13	8	10,000
DMN33D9LV-13A	34B	13	8	10,000

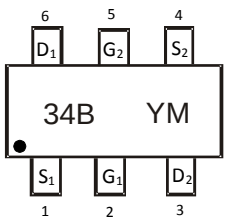
Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

DMN33D9LV-7/-13



DMN33D9LV-7A/-13A (Note 5)



34B = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025
Code	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Note: 5. Part number with suffix 7A and 13A designates devices marked with a Pin 1 indicator. There is no other difference between both devices.

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	350 200	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	0.8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	0.43	W
	T_A = +70°C		0.20	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	288	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current @T_C = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	—	1.4	V	V_{DS} = 3V, I_D = 100µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.2	2.4	Ω	V_{GS} = 10V, I_D = 250mA
		—	0.3	3.0		V_{GS} = 4.5V, I_D = 250mA
		—	0.3	5.0		V_{GS} = 4.0V, I_D = 10mA
		—	0.7	7.0		V_{GS} = 2.5V, I_D = 10mA
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	48	—	pF	V_{DS} = 5V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	11	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	8	—	pF	
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	0.55	—	nC	V_{GS} = 10V, V_{DS} = 10V, I_D = 250mA
Total Gate Charge (V_{GS} = 10V)	Q_g	—	1.23	—	nC	
Gate-Source Charge	Q_{gs}	—	0.14	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.14	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.9	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_G = 25Ω, I_D = 200mA
Turn-On Rise Time	t_R	—	2.6	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	18.2	—	ns	
Turn-Off Fall Time	t_F	—	13.6	—	ns	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

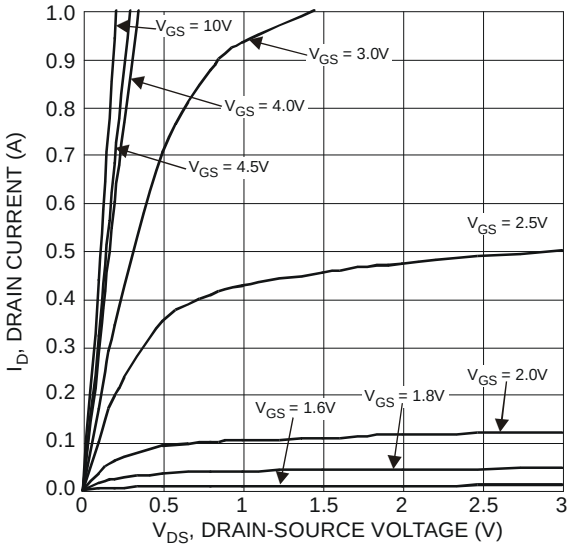


Figure 1 Typical Output Characteristics

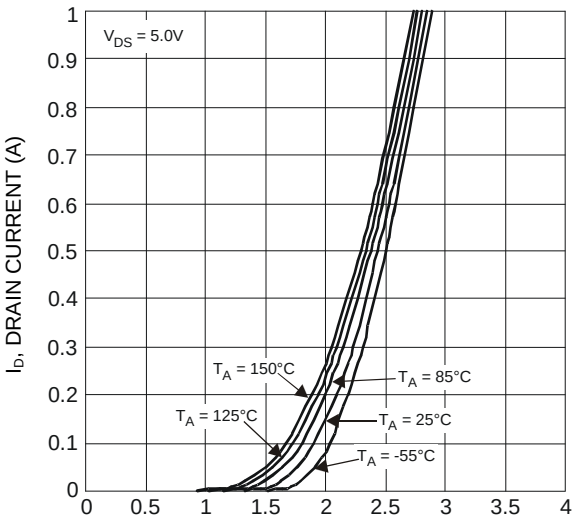


Figure 2 Typical Transfer Characteristics

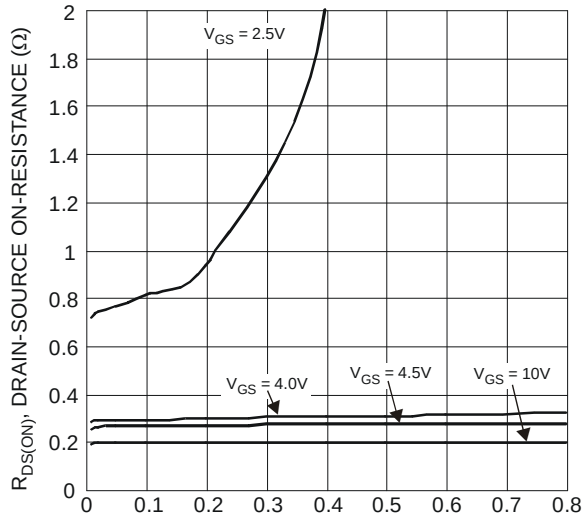


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

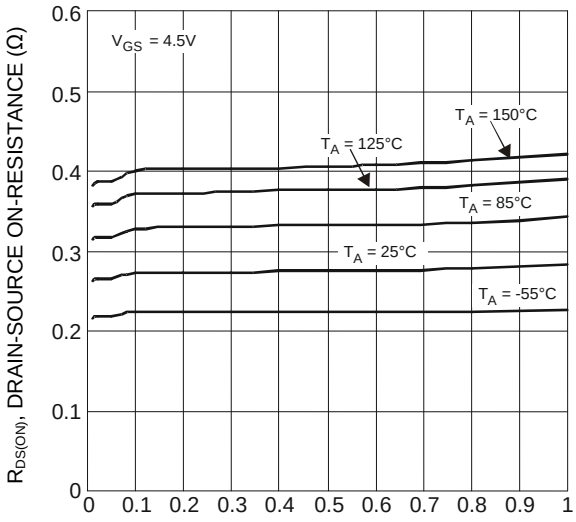


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

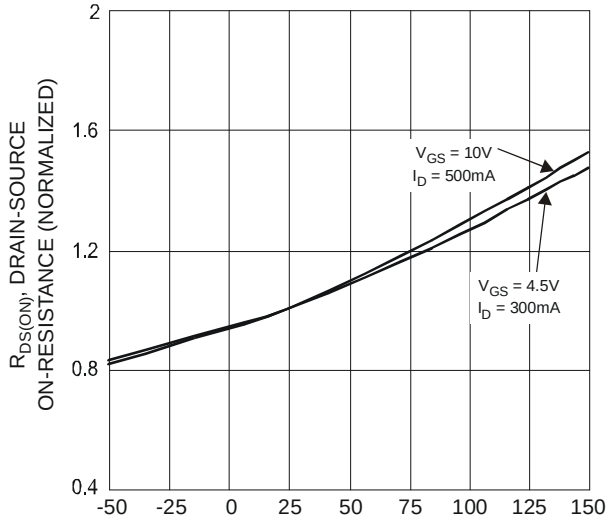


Figure 5 On-Resistance Variation with Temperature

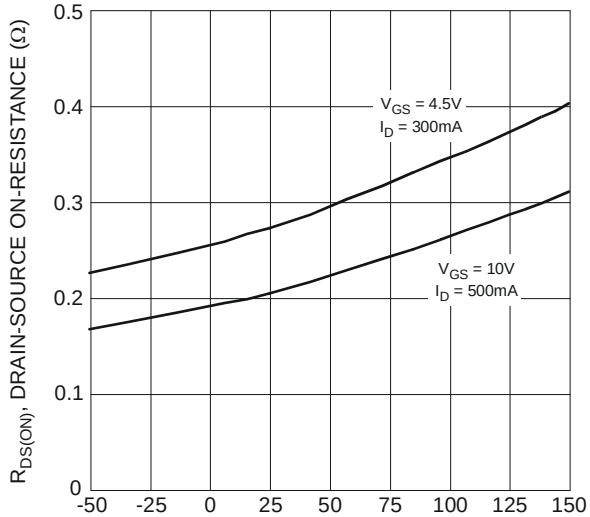


Figure 6 On-Resistance Variation with Temperature

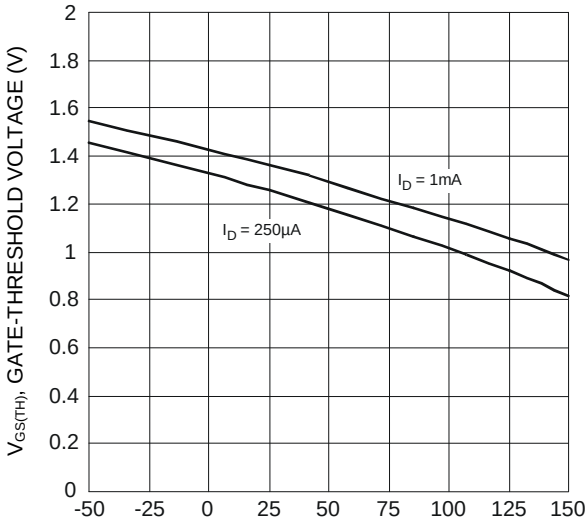


Figure 7 Gate Threshold Variation vs. Junction Temperature

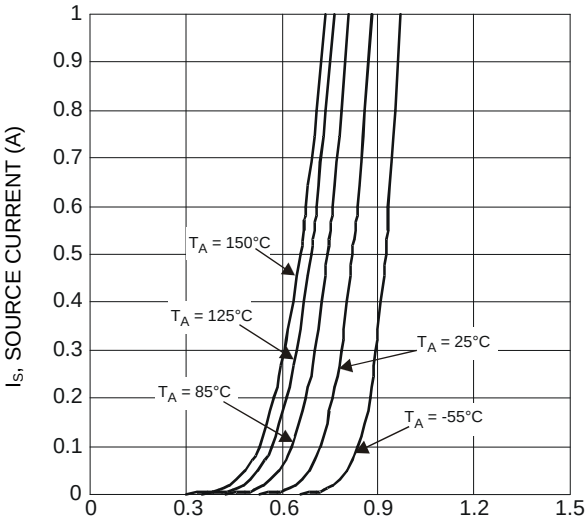


Figure 8 Diode Forward Voltage vs. Current

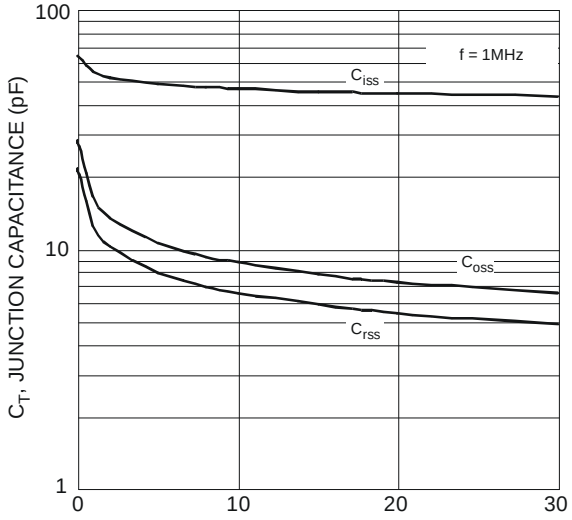


Figure 9 Typical Junction Capacitance

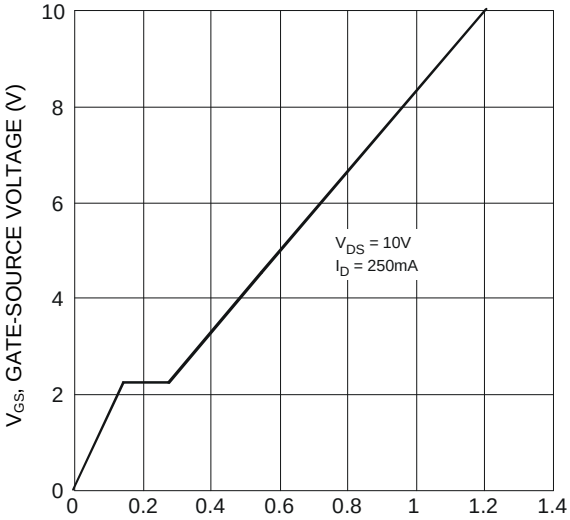


Figure 10 Gate Charge

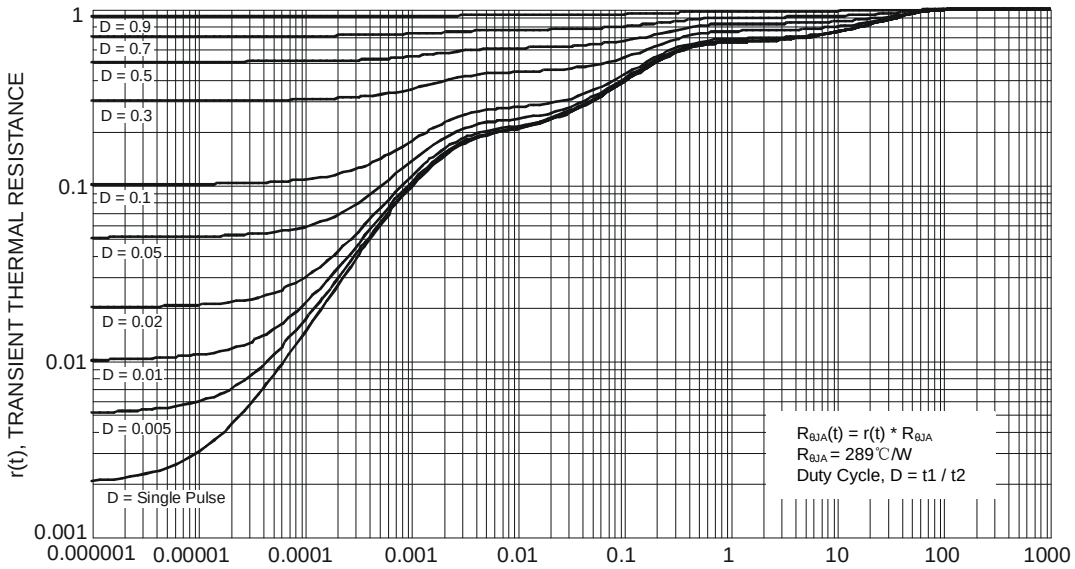


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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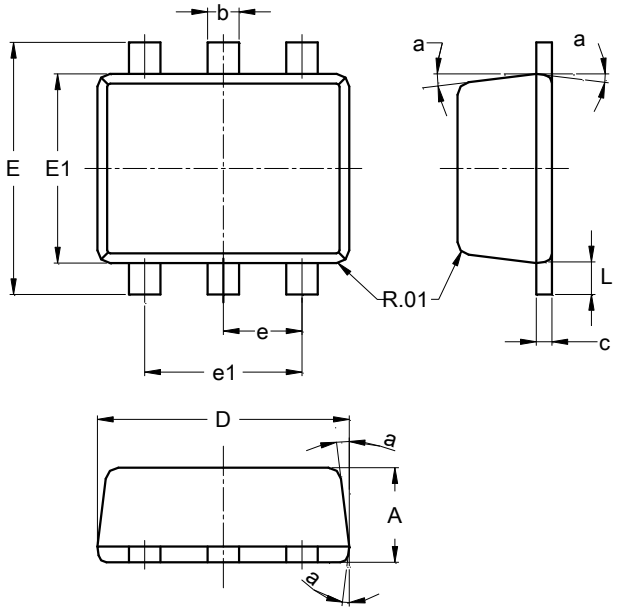

SOT563			
Dim	**Min**	**Max**	**Typ**
A	0.55	0.60	0.60
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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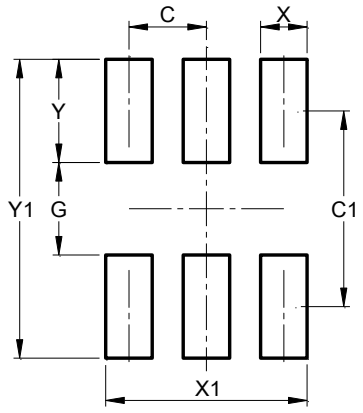

Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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